

Angelica Azcatl

List of Publications by Year in descending order

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Version: 2024-02-01

32
papers

5,113
citations

236925

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454955

30
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32
docs citations

32
times ranked

8701
citing authors

#	ARTICLE	IF	CITATIONS
1	Evaluation of border traps and interface traps in HfO ₂ /MoS ₂ gate stacks by capacitance-voltage analysis. 2D Materials, 2018, 5, 031002.	4.4	63
2	MBE growth of few-layer 2H-MoTe ₂ on 3D substrates. Journal of Crystal Growth, 2018, 482, 61-69.	1.5	43
3	Effects of annealing on top-gated MoS ₂ transistors with HfO ₂ dielectric. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	31
4	Electrical characterization of top-gated molybdenum disulfide field-effect-transistors with high-k dielectrics. Microelectronic Engineering, 2017, 178, 190-193.	2.4	26
5	Schottky Barrier Height of Pd/MoS ₂ Contact by Large Area Photoemission Spectroscopy. ACS Applied Materials & Interfaces, 2017, 9, 38977-38983.	8.0	36
6	Al ₂ O ₃ on WSe ₂ by ozone based atomic layer deposition: Nucleation and interface study. APL Materials, 2017, 5, .	5.1	11
7	Improvement in top-gate MoS ₂ transistor performance due to high quality backside Al ₂ O ₃ layer. Applied Physics Letters, 2017, 111, .	3.3	56
8	Probing Interface Defects in Top-Gated MoS ₂ Transistors with Impedance Spectroscopy. ACS Applied Materials & Interfaces, 2017, 9, 24348-24356.	8.0	38
9	Test structures for understanding the impact of ultra-high vacuum metal deposition on top-gate MoS ₂ field-effect-transistors. , 2017, , .		1
10	Remote Plasma Oxidation and Atomic Layer Etching of MoS ₂ . ACS Applied Materials & Interfaces, 2016, 8, 19119-19126.	8.0	145
11	Covalent Nitrogen Doping and Compressive Strain in MoS ₂ by Remote N ₂ Plasma Exposure. Nano Letters, 2016, 16, 5437-5443.	9.1	323
12	Superacid Passivation of Crystalline Silicon Surfaces. ACS Applied Materials & Interfaces, 2016, 8, 24205-24211.	8.0	38
13	Controllable growth of layered selenide and telluride heterostructures and superlattices using molecular beam epitaxy. Journal of Materials Research, 2016, 31, 900-910.	2.6	85
14	Top-gated MoS ₂ capacitors and transistors with high-k dielectrics for interface study. , 2016, , .		3
15	Partially Fluorinated Graphene: Structural and Electrical Characterization. ACS Applied Materials & Interfaces, 2016, 8, 5002-5008.	8.0	82
16	Highly Scalable, Atomically Thin WSe ₂ Grown <i>via</i> Metal-Organic Chemical Vapor Deposition. ACS Nano, 2015, 9, 2080-2087.	14.6	339
17	HfO ₂ on UV ^o O ₃ exposed transition metal dichalcogenides: interfacial reactions study. 2D Materials, 2015, 2, 014004.	4.4	98
18	Al ₂ O ₃ on Black Phosphorus by Atomic Layer Deposition: An <i>in Situ</i> Interface Study. ACS Applied Materials & Interfaces, 2015, 7, 13038-13043.	8.0	81

#	ARTICLE	IF	CITATIONS
19	A comparative study of atomic layer deposition of Al ₂ O ₃ and HfO ₂ on AlGa _N /Ga _N . Journal of Materials Science: Materials in Electronics, 2015, 26, 4638-4643.	2.2	25
20	Comprehensive structural and optical characterization of MBE grown MoSe ₂ on graphite, CaF ₂ and graphene. 2D Materials, 2015, 2, 024007.	4.4	120
21	Surface and interfacial study of half cycle atomic layer deposited Al ₂ O ₃ on black phosphorus. Microelectronic Engineering, 2015, 147, 1-4.	2.4	15
22	Impurities and Electronic Property Variations of Natural MoS ₂ Crystal Surfaces. ACS Nano, 2015, 9, 9124-9133.	14.6	240
23	Manganese Doping of Monolayer MoS ₂ : The Substrate Is Critical. Nano Letters, 2015, 15, 6586-6591.	9.1	357
24	Near-unity photoluminescence quantum yield in MoS ₂ . Science, 2015, 350, 1065-1068.	12.6	993
25	HfSe ₂ Thin Films: 2D Transition Metal Dichalcogenides Grown by Molecular Beam Epitaxy. ACS Nano, 2015, 9, 474-480.	14.6	195
26	MoS ₂ functionalization for ultra-thin atomic layer deposited dielectrics. Applied Physics Letters, 2014, 104, .	3.3	171
27	<i>In situ</i> x-ray photoelectron spectroscopy and capacitance voltage characterization of plasma treatments for Al ₂ O ₃ /AlGa _N /Ga _N stacks. Applied Physics Letters, 2014, 105, .	3.3	20
28	Hole Contacts on Transition Metal Dichalcogenides: Interface Chemistry and Band Alignments. ACS Nano, 2014, 8, 6265-6272.	14.6	173
29	Hole Selective MoO _x Contact for Silicon Solar Cells. Nano Letters, 2014, 14, 967-971.	9.1	476
30	MoS ₂ P-type Transistors and Diodes Enabled by High Work Function MoO _x Contacts. Nano Letters, 2014, 14, 1337-1342.	9.1	487
31	Atomic Layer Deposition of a High- <i>k</i> Dielectric on MoS ₂ Using Trimethylaluminum and Ozone. ACS Applied Materials & Interfaces, 2014, 6, 11834-11838.	8.0	105
32	HfO ₂ on MoS ₂ by Atomic Layer Deposition: Adsorption Mechanisms and Thickness Scalability. ACS Nano, 2013, 7, 10354-10361.	14.6	237